

SDB30W / AW / CW / SW

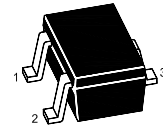
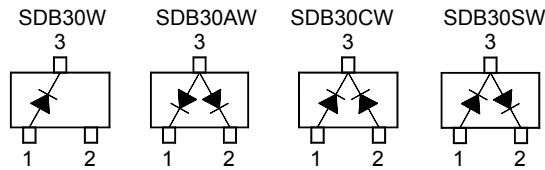
SURFACE MOUNT SCHOTTKY BARRIER DIODE

Features

- Low forward voltage

Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits



SOT-323 Plastic Package

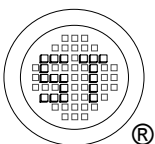
SDB30W Marking Code: L4
 SDB30AW Marking Code: L42
 SDB30CW Marking Code: L43
 SDB30SW Marking Code: L44

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	300	mA
Peak Forward Surge Current ($t_p = 10\text{ ms}$)	I_{FSM}	600	mA
Total Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction Ambient	R_{thJA}	625	$^\circ\text{C/W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 0.1\text{ mA}$ at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 30\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	-	240 320 400 500 800	mV
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	30	-	V
Reverse Current at $V_R = 25\text{ V}$	I_R	-	2	μA
Total Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	-	10	pF



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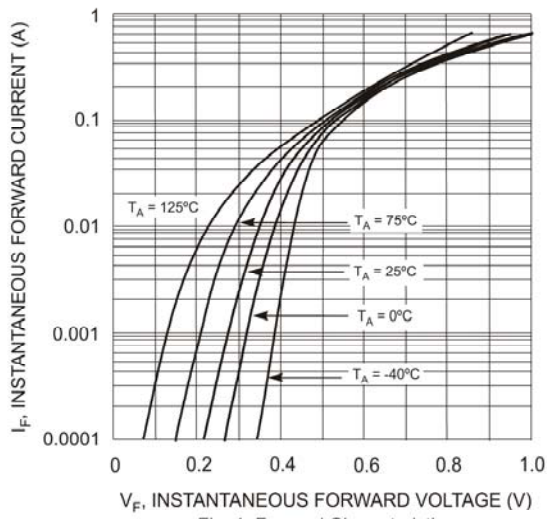


Fig. 1 Forward Characteristics

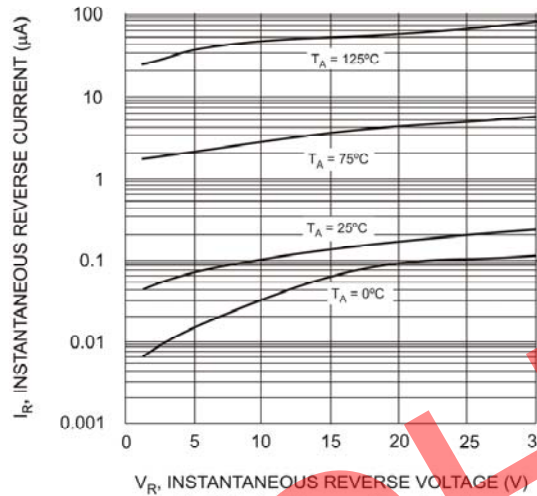


Fig. 2 Typical Reverse Characteristics

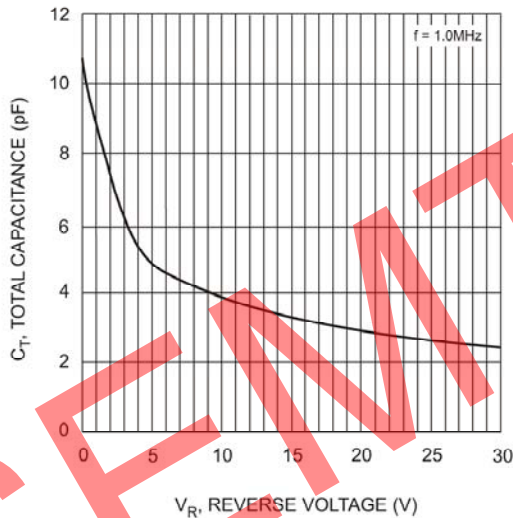


Fig. 3 Typical Capacitance vs. Reverse Voltage

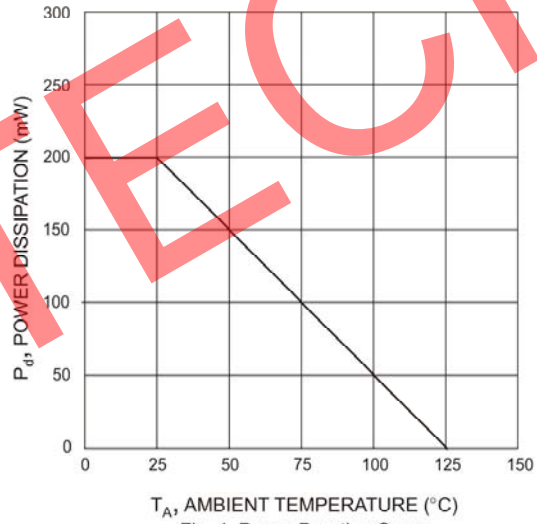
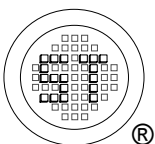


Fig. 4 Power Derating Curve



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